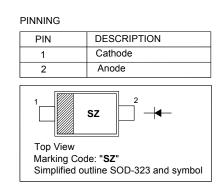
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

- · Super-high speed switching circuit
- Small current rectification



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	30	V
Reverse Voltage	V _R	30	V
Average Forward Current	Ι _Ο	200	mA
Maximum (Peak) Forward Current	I _{FM}	300	mA
Non-repetitive Peak Forward Surge Current 1)	I _{FSM}	1	А
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _s	- 55 to + 150	°C

¹⁾ The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

Characteristics at T_a = 25 °C

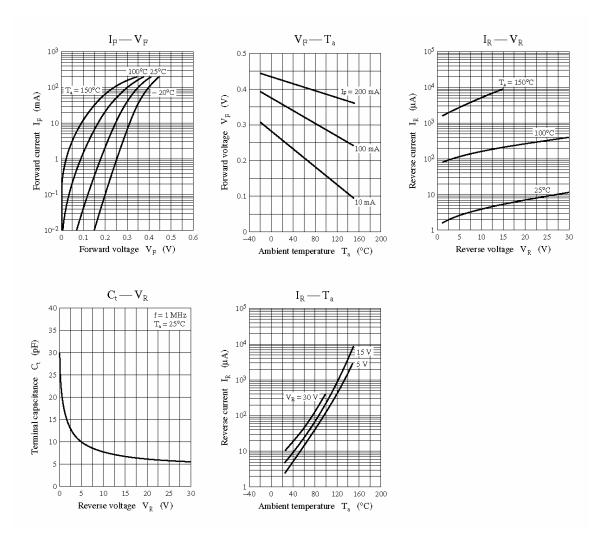
Parameter	Symbol	Тур.	Max.	Unit
Forward Voltage at I _F = 200 mA	V _F	-	0.55	V
Reverse Current at V _R = 30 V	I _R	-	50	μA
Terminal Capacitance at f = 1 MHz	Ст	30	-	pF
Reverse Recovery Time at $I_F = I_R = 100$ mA, $I_{rr} = 10$ mA, $R_L = 100 \Omega$	t _{rr}	3	-	ns







Dated : 01/09/2006







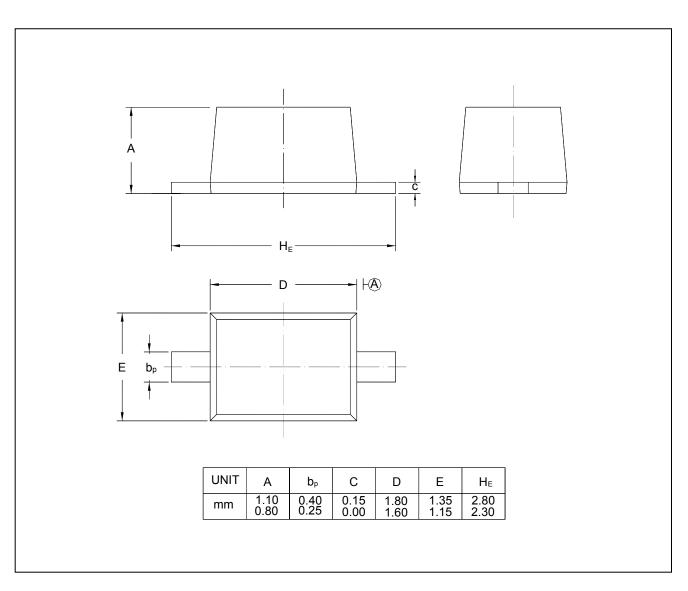


Dated : 01/09/2006

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323









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